

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims

1. (Previously Presented) A polishing system, comprising:

a polishing pad;

a spray element adapted to spray a pressurized fluid upon the polishing pad to remove matter adhered to the pad, wherein said matter is adhered to the polishing pad during a polishing process of a semiconductor topography, and wherein the spray element is configured to be arranged adjacent to an edge of the semiconductor topography which the polishing pad is moving away from during the polishing process; and

a dispense component adapted to dispense a polishing fluid onto the polishing pad during said polishing process, wherein the dispense component is configured to be arranged adjacent to an opposite edge of the semiconductor topography which the polishing pad is moving toward during the polishing process.

2. (Canceled)

3. (Previously Presented) The system of claim 1, wherein said matter comprises particles from the polishing fluid.

4. (Original) The system of claim 1, wherein said matter comprises particles from the semiconductor topography.

5. (Original) The system of claim 1, adapted to allow the pressurized fluid to be dispensed across the entirety of the polishing pad.

6. (Original) The system of claim 1, wherein the spray element is positioned across at least half of the width of the polishing pad.

7. (Original) The system of claim 6, wherein the polishing pad comprises a circular pad and the spray element extends across the radius of the polishing pad.

8. (Original) The system of claim 6, wherein the polishing pad comprises a belt and the spray element extends across the width of the belt.

9. (Original) The system of claim 1, wherein said polishing pad comprises a plurality of pores, and wherein a portion of the matter is embedded within one or more of the pores.

10. (Original) The system of claim 1, wherein the spray element is adapted to be removed from the system.

11. (Currently Amended) A spray element adapted to be positioned within a polishing system and further adapted to remove matter adhered to a polishing pad of the system by spraying a pressurized fluid upon the polishing pad, wherein the spray element comprises;

a plurality of nozzles configured to spray the pressurized fluid; and

one or more adjustable shields arranged about the plurality of nozzles and configured to move independent of an arm comprising the nozzles.

12. (Previously Presented) The spray element of claim 11, wherein the spray element is adapted to be positioned within the polishing system such that the pressurized fluid is dispersed across a region extending across at least half of the width of the polishing pad.

13. (Cancelled)

14. (Previously Presented) The spray element of claim 11, wherein a spray distribution from one of said plurality nozzles overlaps a spray distribution from an adjacent nozzle.

15. (Cancelled)

16. (Previously Presented) The spray element of claim 11, wherein said shields are arranged along the sides of the spray element parallel to the projection of the nozzles.

17. (Previously Presented) The spray element of claim 11, comprising a mounting structure with which to couple the spray element to the polishing system.

18. (Previously Presented) A method for cleaning a polishing pad, comprising:

moving the polishing pad relative to a spray element, wherein the spray element and polishing pad are positioned within a polishing system such that fluid openings of the spray element are positioned toward the polishing pad;

spraying a pressurized fluid in a pulsating sequence from the spray element upon the polishing pad during said moving; and

removing matter adhered to the polishing pad.

19. (Previously Presented) The method of claim 18, wherein said spraying is conducted after polishing one or more semiconductor topographies with the polishing system.

20. (Previously Presented) The method of claim 18, wherein the duration of said spraying is sufficient such that the pressurized fluid is dispensed across the entire upper surface of the polishing pad.

21. (Previously Presented) The method of claim 18, wherein said spraying comprises spraying the fluid at a sufficient pressure to dislodge the matter adhered to the polishing pad.

22. (Previously Presented) The method of claim 18, wherein said spraying comprises spraying the fluid at a pressure between approximately 25 psi and approximately 45 psi.

23. (Previously Presented) A method for polishing multiple semiconductor topographies, comprising:

moving a polishing pad with respect to a semiconductor topography and a spray element;

polishing the semiconductor topography by positioning it against the moving polishing pad;

measuring an amount of matter adhered to the polishing pad subsequent to said polishing;

spraying a pressurized fluid from the spray element upon the polishing pad while moving the polishing pad, wherein said spraying is conducted based upon the amount of matter measured; and

removing matter adhered to the polishing pad.

24. (Previously Presented) The method of claim 23, further comprising polishing one or more additional topographies prior to said measuring.

25. ~ 26. (Canceled)

27. (Previously Presented) The method of claim 18, wherein said spraying is conducted simultaneously with polishing one or more semiconductor topographies with the polishing system.

28. (Previously Presented) The method of claim 23, further comprising applying a polishing fluid from a dispense component prior to said polishing.